Transistors 2SC815

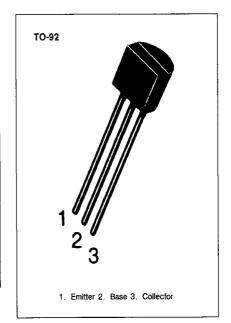


LOW FREQUENCY AMPLIFIER HIGH FREQUENCY OSCILLATOR

- Complement to KSA539
- www.DataSheeCollector-Base Voltage V_{CBO} = 60V

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EBO}	5	ν
Collector Current	l _c	200	mA
Collector Dissipation	Pc	400	mW
Junction Temperature	Ti 1	150	°C
Storage Temperature	Tstg	−55∼150	°C



ELECTRICAL CHARACTERISTICS (Ta=25°C)

Characteristic	Symbol	Test Conditions	Min	Тур	Max	Unit
Collector-Base Breakdown Voltage Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cut-off Current Emitter Cut-off Current DC Current Gain Base-Emitter On Voltage Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage Current Gain-Bandwidth Product Output Capacitance	BVCBO BVCEO BVEBO ICBO IEBO hFE VBE (on) VCE (sat) VBE (sat) fT Cob	$I_C = 100\mu A$, $I_E = 0$ $I_C = 10mA$, $I_B = 0$ $I_E = 10\mu A$, $I_C = 0$ $V_{CB} = 45V$, $I_C = 0$ $V_{CE} = 1V$, $I_C = 50mA$ $V_{CE} = 10V$, $I_C = 10mA$ $I_C = 150mA$, $I_B = 15mA$ $I_C = 150mA$, $I_B = 15mA$ $V_{CE} = 10V$, $I_C = 10mA$ $V_{CB} = 10V$, $I_C = 10mA$ $V_{CB} = 10V$, $I_C = 10mA$ $V_{CB} = 10V$, $I_C = 10mA$	60 45 5 40 0.6	0.65 0.15 0.83 200 4	0.1 0.1 400 0.9 0.4 1.1	V V V μA μA V V V MHz pF

h_{FE} CLASSIFICATION

Classification	R	0	Y	G
h _{FE}	40-80	70-140	120-240	200-400



